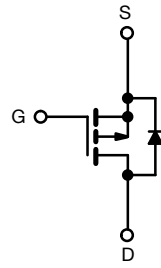
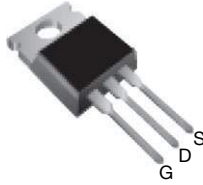


## Power MOSFET

**TO-220AB**


P-Channel MOSFET

### FEATURES

- Dynamic dV/dt rating
- Repetitive avalanche rated
- P-channel
- 175 °C operating temperature
- Fast switching
- Ease of paralleling
- Simple drive requirements
- Material categorization: for definitions of compliance please see [www.vishay.com/doc?99912](http://www.vishay.com/doc?99912)



### Note

\* This datasheet provides information about parts that are RoHS-compliant and / or parts that are non RoHS-compliant. For example, parts with lead (Pb) terminations are not RoHS-compliant. Please see the information / tables in this datasheet for details

### DESCRIPTION

Third generation power MOSFETs from Vishay provide the designer with the best combination of fast switching, ruggedized device design, low on-resistance and cost-effectiveness.

The TO-220AB package is universally preferred for all commercial-industrial applications at power dissipation levels to approximately 50 W. The low thermal resistance and low package cost of the TO-220AB contribute to its wide acceptance throughout the industry.

### PRODUCT SUMMARY

$V_{DS}$ (V)	-100	
$R_{DS(on)}$ ( $\Omega$ )	$V_{GS} = -10$ V	0.30
$Q_g$ max. (nC)	38	
$Q_{gs}$ (nC)	6.8	
$Q_{gd}$ (nC)	21	
Configuration	Single	

### ORDERING INFORMATION

Package	TO-220AB
Lead (Pb)-free	IRF9530PbF
Lead (Pb)-free and halogen-free	IRF9530PbF-BE3

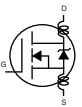

### ABSOLUTE MAXIMUM RATINGS ( $T_C = 25$ °C, unless otherwise noted)

PARAMETER	SYMBOL	LIMIT	UNIT	
Drain-source voltage	$V_{DS}$	-100	V	
Gate-source voltage	$V_{GS}$	$\pm 20$		
Continuous drain current	$V_{GS}$ at 10 V	$T_C = 25$ °C	-12	A
		$T_C = 100$ °C	-8.2	
Pulsed drain current <sup>a</sup>	$I_{DM}$	-48		
Linear derating factor		0.59	W/°C	
Single pulse avalanche energy <sup>b</sup>	$E_{AS}$	400	mJ	
Repetitive avalanche current <sup>a</sup>	$I_{AR}$	-12	A	
Repetitive avalanche energy <sup>a</sup>	$E_{AR}$	8.8	mJ	
Maximum power dissipation	$T_C = 25$ °C	$P_D$	88	W
Peak diode recovery dV/dt <sup>c</sup>		dV/dt	- 5.5	V/ns
Operating junction and storage temperature range	$T_J, T_{stg}$		-55 to +175	°C
Soldering recommendations (peak temperature) <sup>d</sup>	For 10 s		300	
Mounting torque	6-32 or M3 screw		10	lbf · in
			1.1	N · m

### Notes

- Repetitive rating; pulse width limited by maximum junction temperature (see fig. 11)
- $V_{DD} = -25$  V, starting  $T_J = 25$  °C,  $L = 4.2$  mH,  $R_g = 25$   $\Omega$ ,  $I_{AS} = -12$  A (see fig. 12)
- $I_{SD} \leq -12$  A,  $di/dt \leq 140$  A/ $\mu$ s,  $V_{DD} \leq V_{DS}$ ,  $T_J \leq 175$  °C
- 1.6 mm from case

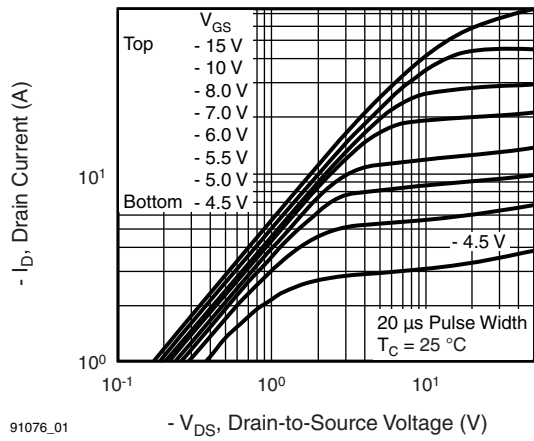
THERMAL RESISTANCE RATINGS				
PARAMETER	SYMBOL	TYP.	MAX.	UNIT
Maximum junction-to-ambient	$R_{thJA}$	-	62	°C/W
Case-to-sink, flat, greased surface	$R_{thCS}$	0.50	-	
Maximum junction-to-case (drain)	$R_{thJC}$	-	1.7	

SPECIFICATIONS ( $T_J = 25\text{ }^\circ\text{C}$ , unless otherwise noted)							
PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNIT
<b>Static</b>							
Drain-source breakdown voltage	$V_{DS}$	$V_{GS} = 0\text{ V}, I_D = -250\text{ }\mu\text{A}$		-100	-	-	V
$V_{DS}$ temperature coefficient	$\Delta V_{DS}/T_J$	Reference to $25\text{ }^\circ\text{C}$ , $I_D = -1\text{ mA}$		-	-0.10	-	V/°C
Gate-source threshold voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = -250\text{ }\mu\text{A}$		-2.0	-	-4.0	V
Gate-source leakage	$I_{GSS}$	$V_{GS} = \pm 20\text{ V}$		-	-	$\pm 100$	nA
Zero gate voltage drain current	$I_{DSS}$	$V_{DS} = -100\text{ V}, V_{GS} = 0\text{ V}$		-	-	-100	$\mu\text{A}$
		$V_{DS} = -80\text{ V}, V_{GS} = 0\text{ V}, T_J = 150\text{ }^\circ\text{C}$		-	-	-500	
Drain-source on-state resistance	$R_{DS(on)}$	$V_{GS} = -10\text{ V}$	$I_D = -7.2\text{ A}^b$	-	-	0.30	$\Omega$
Forward transconductance	$g_{fs}$	$V_{DS} = -50\text{ V}, I_D = -7.2\text{ A}^b$		3.7	-	-	S
<b>Dynamic</b>							
Input capacitance	$C_{iss}$	$V_{GS} = 0\text{ V},$ $V_{DS} = -25\text{ V},$ $f = 1.0\text{ MHz, see fig. 5}$		-	860	-	$\mu\text{F}$
Output capacitance	$C_{oss}$			-	340	-	
Reverse transfer capacitance	$C_{rss}$			-	93	-	
Total gate charge	$Q_g$	$V_{GS} = -10\text{ V}$	$I_D = -12\text{ A}, V_{DS} = -80\text{ V},$ see fig. 6 and 13 <sup>b</sup>	-	-	38	nC
Gate-source charge	$Q_{gs}$			-	-	6.8	
Gate-drain charge	$Q_{gd}$			-	-	21	
Turn-on delay time	$t_{d(on)}$	$V_{DD} = -50\text{ V}, I_D = -12\text{ A},$ $R_g = 12\text{ }\Omega, R_D = 3.9\text{ }\Omega,$ see fig. 10 <sup>b</sup>		-	12	-	ns
Rise time	$t_r$			-	52	-	
Turn-off delay time	$t_{d(off)}$			-	31	-	
Fall time	$t_f$			-	39	-	
Gate input resistance	$L_D$	Between lead, 6 mm (0.25") from package and center of die contact 		-	4.5	-	nH
Internal drain inductance	$L_S$			-	7.5	-	
Internal source inductance	$R_g$	$f = 1\text{ MHz, open drain}$		0.4	-	3.3	$\Omega$
<b>Drain-Source Body Diode Characteristics</b>							
Continuous source-drain diode current	$I_S$	MOSFET symbol showing the integral reverse p-n junction diode 		-	-	-12	A
Pulsed diode forward current <sup>a</sup>	$I_{SM}$			-	-	-48	
Body diode voltage	$V_{SD}$	$T_J = 25\text{ }^\circ\text{C}, I_S = -12\text{ A}, V_{GS} = 0\text{ V}^b$		-	-	-6.3	V
Body diode reverse recovery time	$t_{rr}$	$T_J = 25\text{ }^\circ\text{C}, I_F = -12\text{ A}, dI/dt = 100\text{ A}/\mu\text{s}^b$		-	120	240	ns
Body diode reverse recovery charge	$Q_{rr}$			-	0.46	0.92	$\mu\text{C}$
Forward turn-on time	$t_{on}$	Intrinsic turn-on time is negligible (turn-on is dominated by $L_S$ and $L_D$ )					

**Notes**

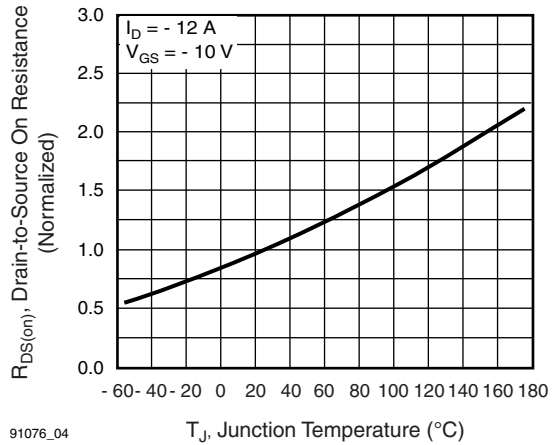
- a. Repetitive rating; pulse width limited by maximum junction temperature (see fig. 11)  
 b. Pulse width  $\leq 300\text{ }\mu\text{s}$ ; duty cycle  $\leq 2\%$

**TYPICAL CHARACTERISTICS** (25 °C, unless otherwise noted)



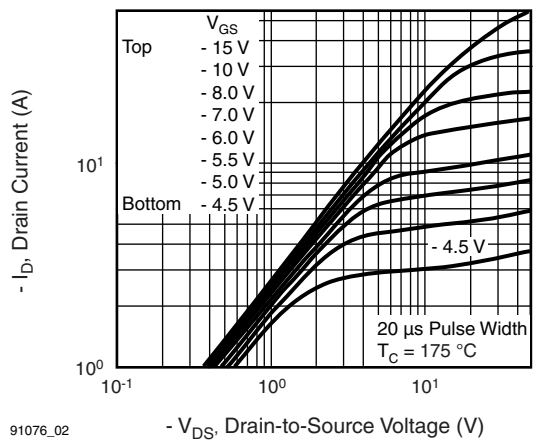
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**Fig. 1 - Typical Output Characteristics, T<sub>C</sub> = 25 °C**



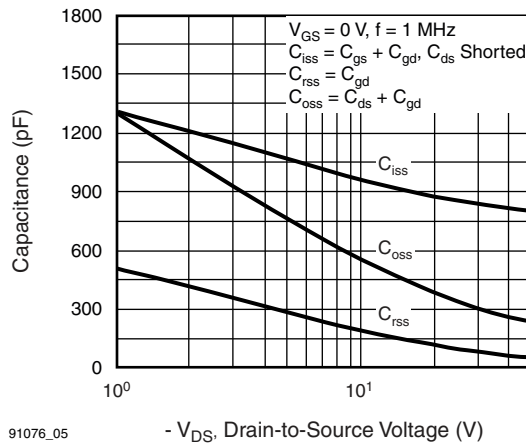
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**Fig. 4 - Normalized On-Resistance vs. Temperature**



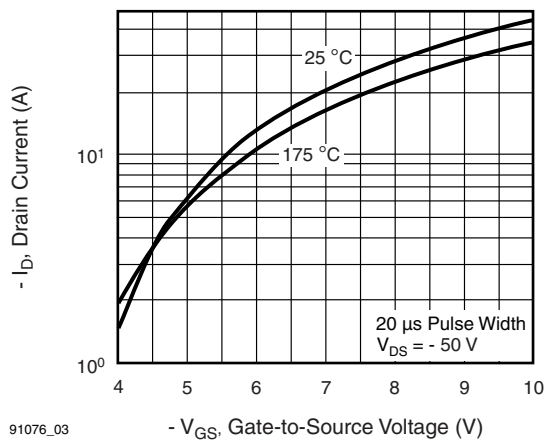
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**Fig. 2 - Typical Output Characteristics, T<sub>C</sub> = 175 °C**



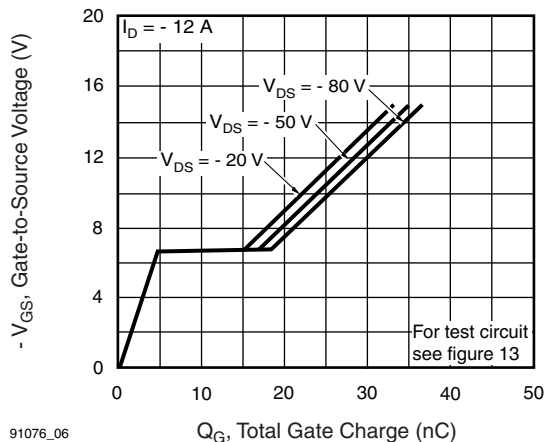
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**Fig. 5 - Typical Capacitance vs. Drain-to-Source Voltage**



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**Fig. 3 - Typical Transfer Characteristics**



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**Fig. 6 - Typical Gate Charge vs. Gate-to-Source Voltage**

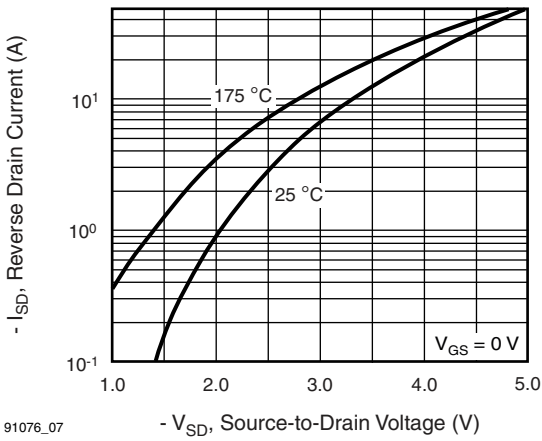


Fig. 7 - Typical Source-Drain Diode Forward Voltage

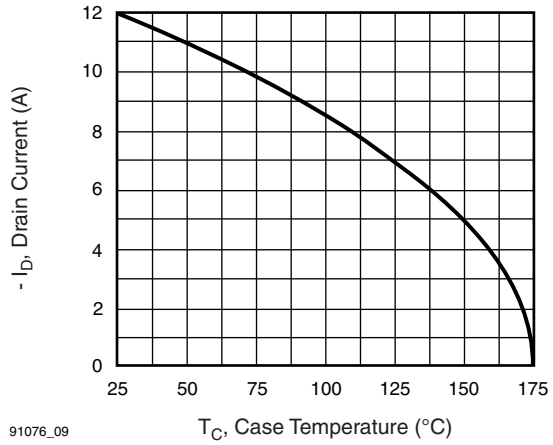


Fig. 9 - Maximum Drain Current vs. Case Temperature

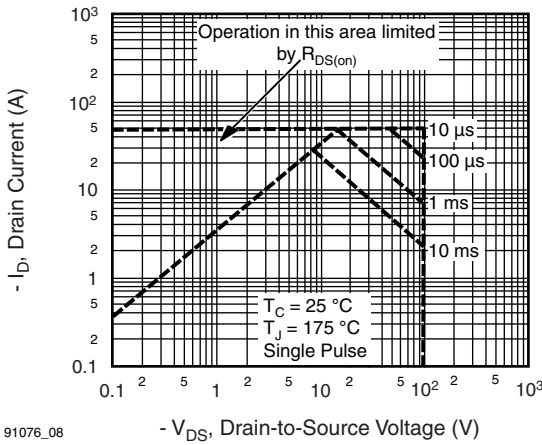


Fig. 8 - Maximum Safe Operating Area

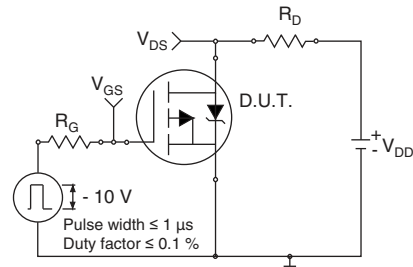


Fig. 10 - Switching Time Test Circuit

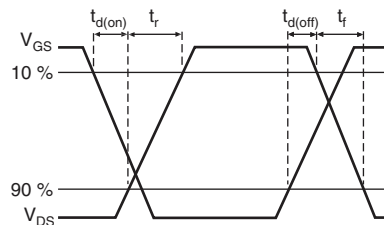


Fig. 11 - Switching Time Waveforms

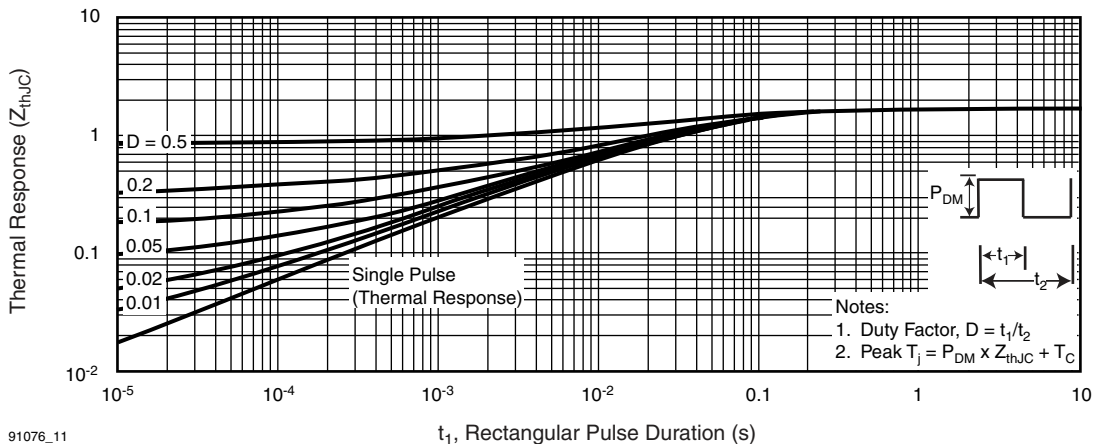


Fig. 12 - Maximum Effective Transient Thermal Impedance, Junction-to-Case

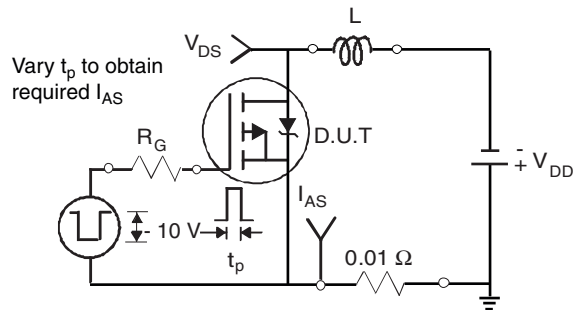


Fig. 13 - Unclamped Inductive Test Circuit

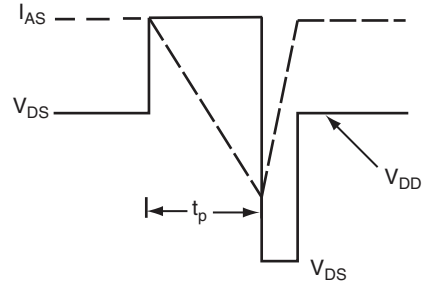


Fig. 14 - Unclamped Inductive Waveforms

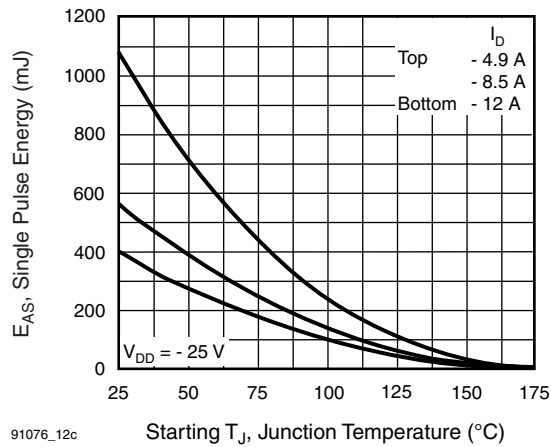


Fig. 15 - Maximum Avalanche Energy vs. Drain Current

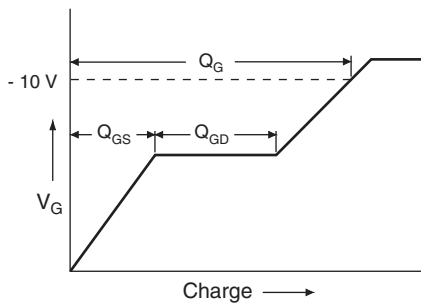


Fig. 16 - Basic Gate Charge Waveform

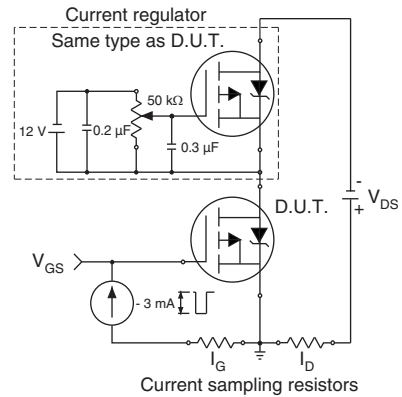
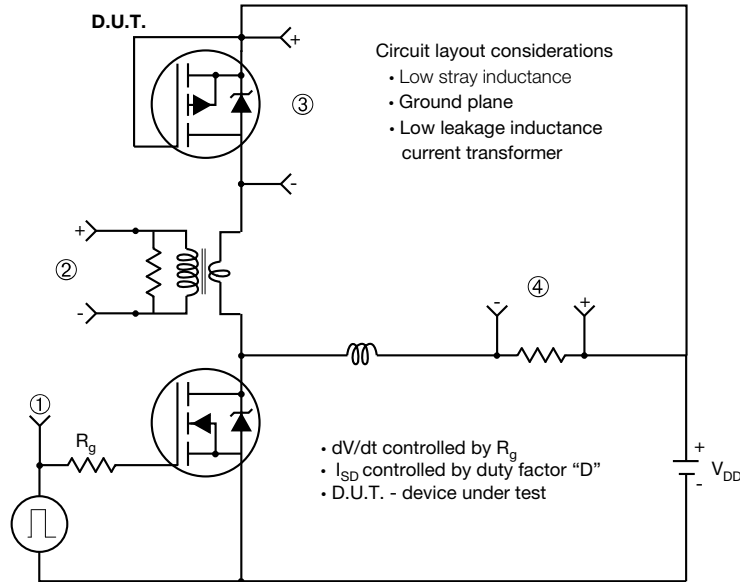
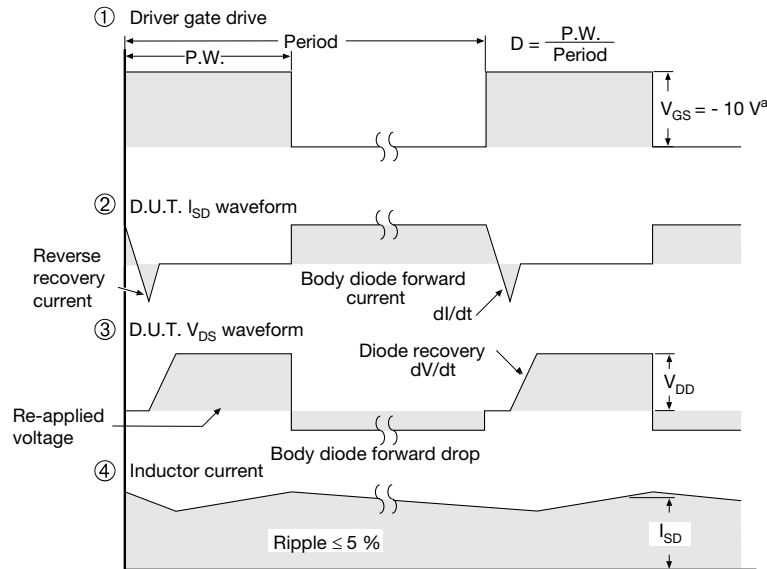


Fig. 17 - Gate Charge Test Circuit

**Peak Diode Recovery dV/dt Test Circuit**



**Note**  
 • Compliment N-Channel of D.U.T. for driver

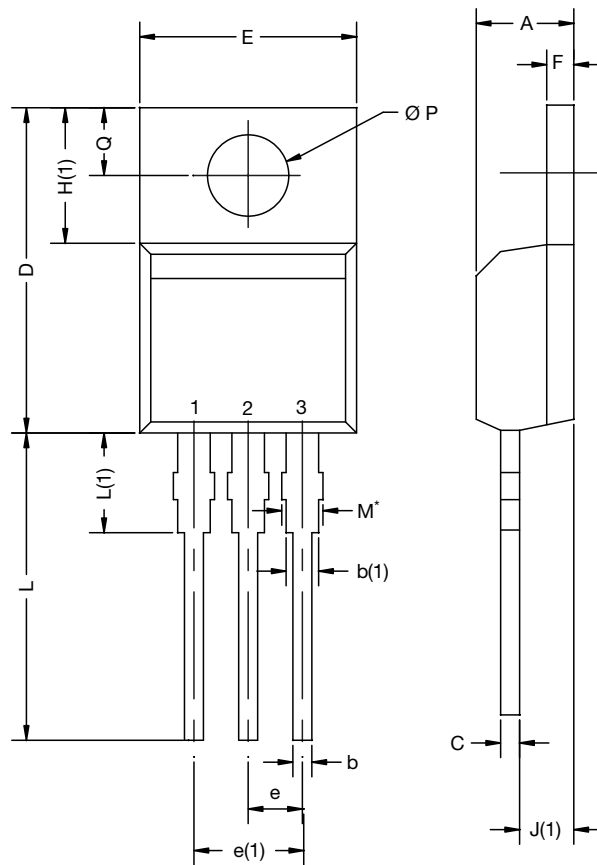


**Note**  
 a.  $V_{GS} = -5\text{ V}$  for logic level and  $-3\text{ V}$  drive devices

**Fig. 18 - For P-Channel**

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### TO-220-1



DIM.	MILLIMETERS		INCHES	
	MIN.	MAX.	MIN.	MAX.
A	4.24	4.65	0.167	0.183
b	0.69	1.02	0.027	0.040
b(1)	1.14	1.78	0.045	0.070
c	0.36	0.61	0.014	0.024
D	14.33	15.85	0.564	0.624
E	9.96	10.52	0.392	0.414
e	2.41	2.67	0.095	0.105
e(1)	4.88	5.28	0.192	0.208
F	1.14	1.40	0.045	0.055
H(1)	6.10	6.71	0.240	0.264
J(1)	2.41	2.92	0.095	0.115
L	13.36	14.40	0.526	0.567
L(1)	3.33	4.04	0.131	0.159
Ø P	3.53	3.94	0.139	0.155
Q	2.54	3.00	0.100	0.118

ECN: E21-0621-Rev. D, 04-Nov-2021  
 DWG: 6031

#### Note

- M\* = 0.052 inches to 0.064 inches (dimension including protrusion), heatsink hole for HVM



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